2. Pinning information

Table 2. Pinning information

Pin Symbol Description 1 G gate 2 D drain 3 S source mb D mounting base; connected to drain		
2 D drain 3 S source mb D mounting base; connected to drain	Graphic symbol	
3 S source mb D mounting base; connected to drain	_	
mb D mounting base; connected to drain	D	
drain		
	mbb076 S	
SOT78 (TO-220AB)		

3. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PSMN015-100P	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78			

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$	-	100	V
V_{DGR}	drain-gate voltage	$T_j \le 175 \text{ °C}; T_j \ge 25 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	100	V
V_{GS}	gate-source voltage		-20	20	V
I_D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	-	60.8	Α
		$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Mode 1}} \text{ and } \frac{3}{\text{Mode 2}}$	-	75	А
I_{DM}	peak drain current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$; see Figure 3	-	240	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	300	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-dr	ain diode				
I _S	source current	$T_{mb} = 25 ^{\circ}C$	-	75	Α
I _{SM}	peak source current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$	-	240	Α
Avalanche	ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 36 A; V_{sup} ≤ 50 V; unclamped; t_p = 0.11 ms; R_{GS} = 50 Ω	-	320	mJ

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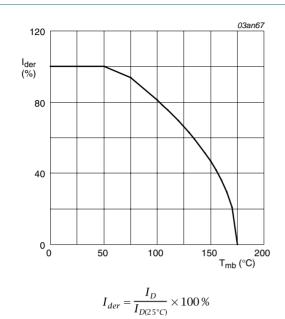
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2 of 12

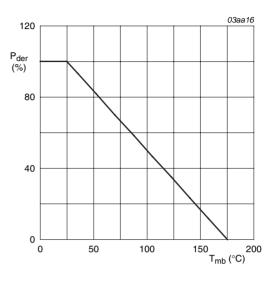
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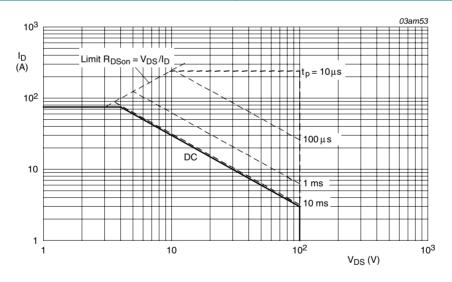
Normalized continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

3 of 12

Normalized total power dissipation as a Fig 2. function of mounting base temperature



 $T_{mb} = 25$ °C; I_{DM} is single pulse; $V_{GS} = 10V$

Safe operating area; continuous and peak drain currents as a function of drain-source voltage Fig 3.

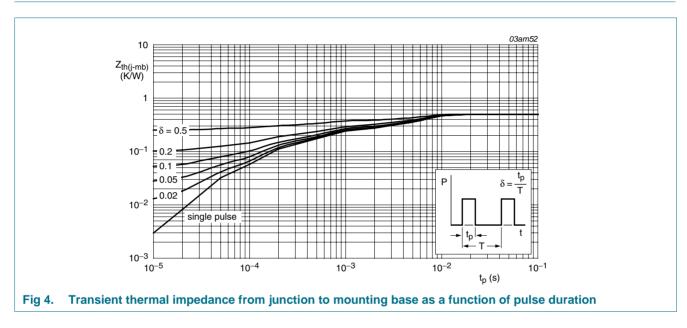
4 of 12

N-channel TrenchMOS SiliconMAX standard level FET

Thermal characteristics

Table 5. **Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j\text{-}mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	0.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in still air	-	60	-	K/W



Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _{(BR)DSS} drain-source		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	89	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	100	-	-	V
V _{GS(th)}	gate-source threshold	$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 175 \text{ °C}$; see Figure 8	1	-	-	V
	voltage	$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = -55 \text{ °C}$; see Figure 8	-	-	4.4	V
		$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 25 \text{ °C}$; see Figure 8	2	3	4	V
I _{DSS}	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μA
		V _{DS} = 100 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure 9}}{\text{Model}}$	-	2	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 9}}{\text{ of } T_j}$	-	2	100	nA
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 ^{\circ}\text{C};$ see Figure 9 and 10	-	32.4	40.5	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 9 and 10	-	12	15	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	I_D = 75 A; V_{DS} = 80 V; V_{GS} = 10 V; T_j = 25 °C; see <u>Figure 11</u>	-	90	-	nC
Q_{GS}	gate-source charge	$I_D = 75 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 11</u>	-	20	-	nC
Q_{GD}	gate-drain charge	$I_D = 75 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 10 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 11</u>	-	35	-	nC
C _{iss}	input capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}; T_j = 25 °C;$	-	4900	-	pF
C _{oss}	output capacitance	see Figure 12		390	-	pF
C _{rss}	reverse transfer capacitance		-	220	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 1.8 \Omega; V_{GS} = 10 \text{ V};$	-	25	-	ns
t _r	rise time	$R_{G(ext)} = 5.6 \Omega; T_j = 25 °C$	-	65	-	ns
t _{d(off)}	turn-off delay time			95	-	ns
t _f	fall time			50	-	ns
Source-di	rain diode					
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see Figure 13	-	8.0	1.1	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}$; $dI_S/dt = -100 \text{ A/}\mu\text{s}$; $V_{GS} = 0 \text{ V}$;	-	80	-	ns
Qr	recovered charge	$V_{DS} = 25 \text{ V}; T_j = 25 \text{ °C}$		115	-	nC

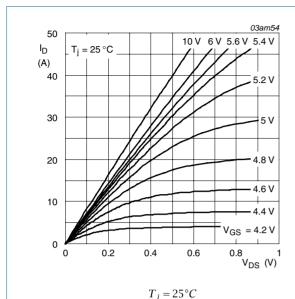


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

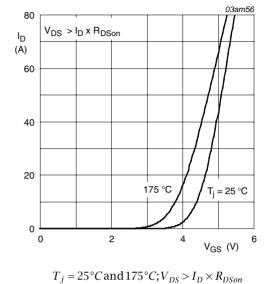
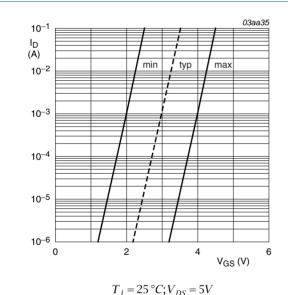


Fig 6. Transfer characteristics: drain current as a

function of gate-source voltage; typical values



Sub-threshold drain current as a function of gate-source voltage

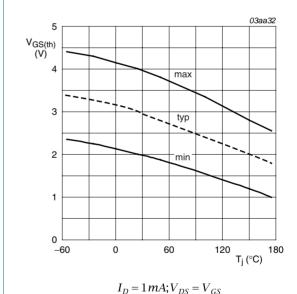


Fig 8. Gate-source threshold voltage as a function of junction temperature

6 of 12

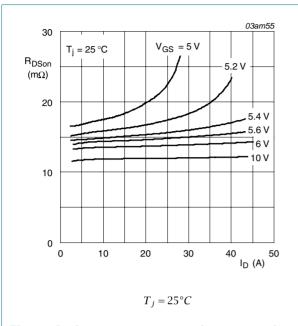


Fig 9. Drain-source on-state resistance as a function of drain current; typical values

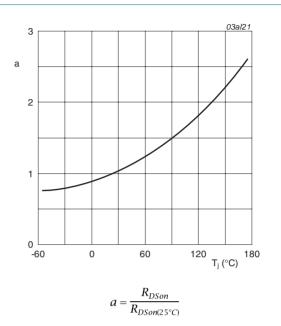


Fig 10. Normalized drain-source on-state resistance factor as a function of junction temperature

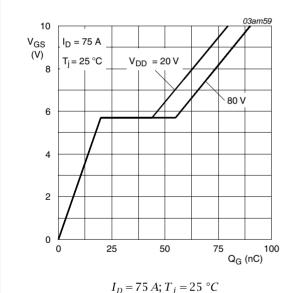
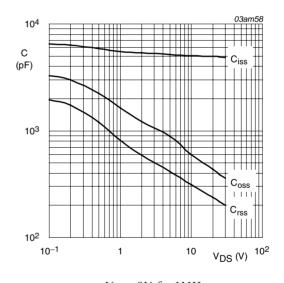


Fig 11. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0V; f = 1MHz$

Fig 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

Product data sheet

7 of 12

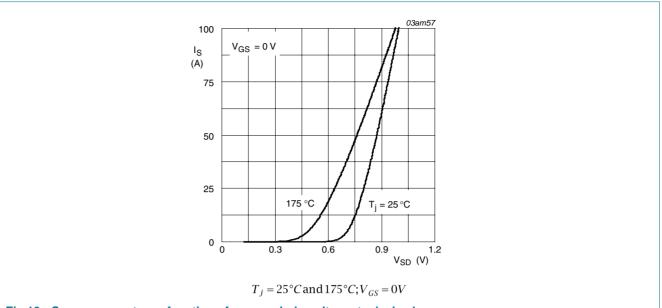


Fig 13. Source current as a function of source-drain voltage; typical values

7. Package outline

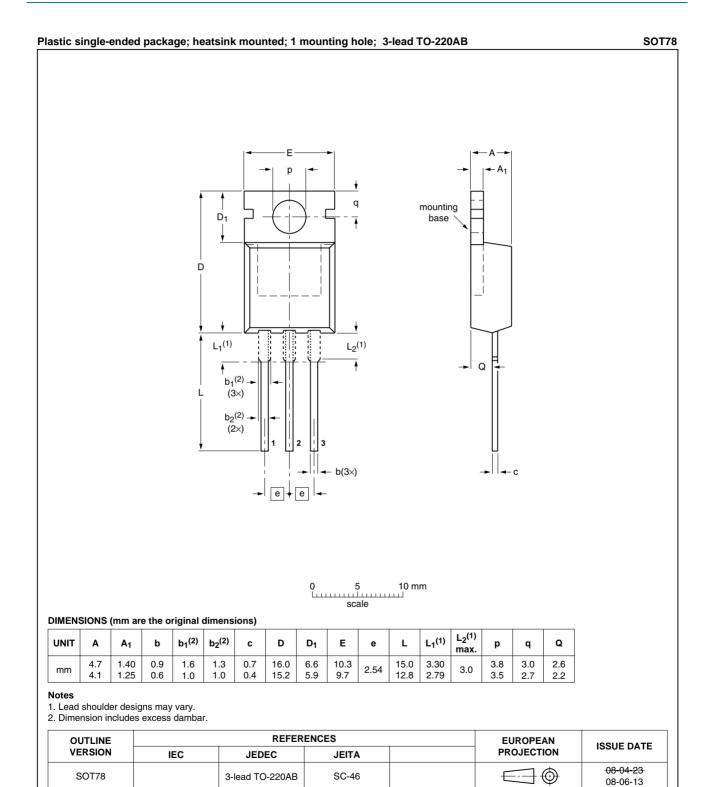


Fig 14. Package outline SOT78 (TO-220AB)

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10 of 12

N-channel TrenchMOS SiliconMAX standard level FET

Revision history

Table 7. **Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN015-100P_6	20091217	Product data sheet	-	PSMN015_100P_100B-05
Modifications:		at of this data sheet ha s of NXP Semiconduct	•	d to comply with the new identity
	 Legal text 	ts have been adapted	to the new compa	ny name where appropriate.
	 Type num 	ber PSMN015-100P s	eparated from dat	a sheet PSMN015_100P_100B-05
PSMN015_100P_100B-05	20040114	Product data	-	PSMN015-100_SERIES_4
PSMN015-100_SERIES_4	20030601	Product specification	-	PSMN015-100_SERIES_HG_3
PSMN015-100_SERIES_HG_3	20000328	Product specification	-	PSMN015-100_SERIES_2
PSMN015-100_SERIES_2	19990801	Product specification	-	PSMN015-100_SERIES_1
PSMN015-100_SERIES_1	19990201	Product specification	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nexperia.com.

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11. Contents

1	Product profile
1.1	General description1
1.2	Features and benefits1
1.3	Applications1
1.4	Quick reference data1
2	Pinning information
3	Ordering information
4	Limiting values
5	Thermal characteristics4
6	Characteristics5
7	Package outline
8	Revision history10
9	Legal information11
9.1	Data sheet status
9.2	Definitions
9.3	Disclaimers
9.4	Trademarks11
10	Contact information 11